

Exchange bias field change of FeMn/NiFe bilayer thin films by He ion irradiation.

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Abstract

Exchange bias in the interfaces of NiFe/ FeMn films by He ion irradiation using DuoPIGatron Ion source is investigated. Magneto-optic Kerr effect measurement (MOKE) and VSM carry out on sputtered exchange biased films before and after NiFe/FeMn thin film system before and after irradiation shows a modification of the Exchange bias field with irradiation. This modification first an increase in the exchange bias followed, with successive ion doses, by a reduction. For higher ion dose the exchange bias field is decreased and finally completely suppressed.

References

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